

## Description

The VST10N030 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(on)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

## General Features

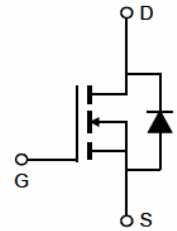
- $V_{DS} = 100V, I_D = 150A$   
 $R_{DS(on)} < 3.6m\Omega @ V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

## Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



TO-263



Schematic Diagram

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST10N030-T3	VST10N030	TO-263	-	-	-

## Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous (Silicon Limited)	$I_D$	170	A
Drain Current-Continuous (Package Limited)	$I_D$	150	A
Drain Current-Continuous ( $T_C = 100^\circ\text{C}$ )	$I_D (100^\circ\text{C})$	120	A
Pulsed Drain Current	$I_{DM}$	600	A
Maximum Power Dissipation	$P_D$	250	W
Derating factor		1.67	W/ $^\circ\text{C}$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	1500	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ\text{C}$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	0.6	$^\circ\text{C/W}$
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**Electrical Characteristics ( $T_C=25^{\circ}\text{C}$  unless otherwise noted)**

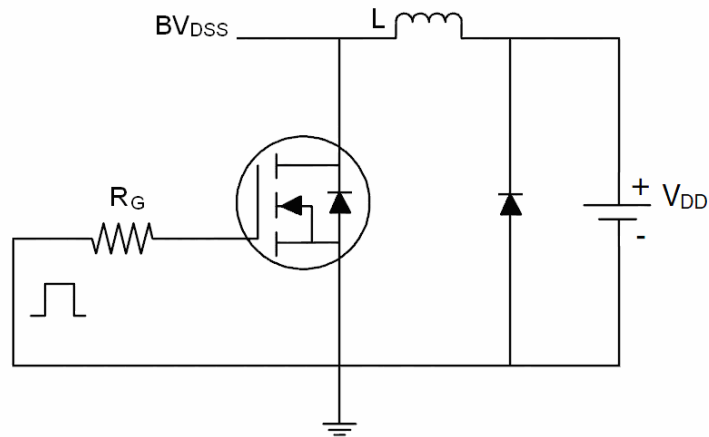
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics <sup>(Note 3)</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =75A	-	3.0	3.6	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =75A	75	-	-	S
Dynamic Characteristics <sup>(Note4)</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, F=1.0MHz	-	7770	-	PF
Output Capacitance	C <sub>oss</sub>		-	795	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	46	-	PF
Switching Characteristics <sup>(Note 4)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =50V, I <sub>D</sub> =75A V <sub>GS</sub> =10V, R <sub>G</sub> =4.7Ω	-	25	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	80	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	52	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	17	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =75A, V <sub>GS</sub> =10V	-	113		nC
Gate-Source Charge	Q <sub>gs</sub>		-	39.5		nC
Gate-Drain Charge	Q <sub>gd</sub>		-	25.6		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =150A	-		1.2	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>		-	-	150	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub> di/dt = 100A/μs <sup>(Note3)</sup>	-	75		nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	168		nC

**Notes:**

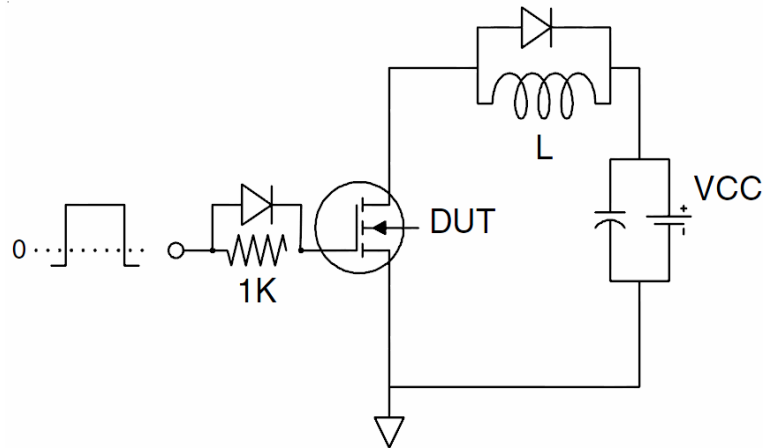
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$

## Test Circuit

### 1) $E_{AS}$ test Circuit



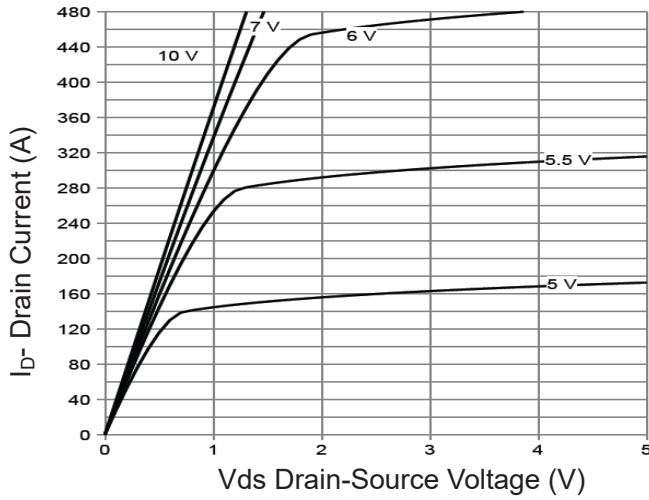
### 2) Gate charge test Circuit



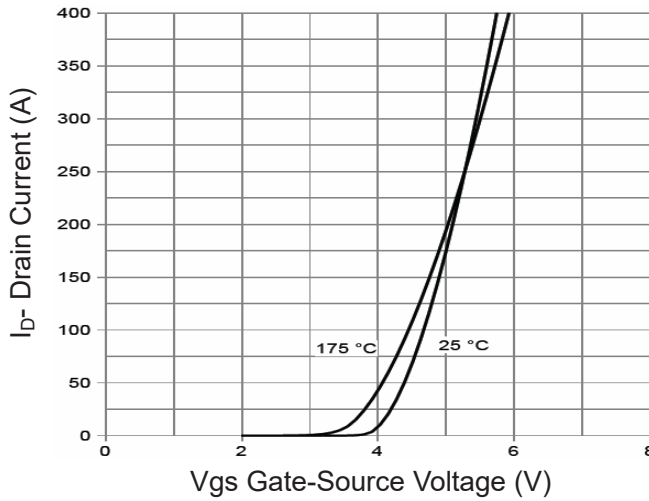
### 3) Switch Time Test Circuit



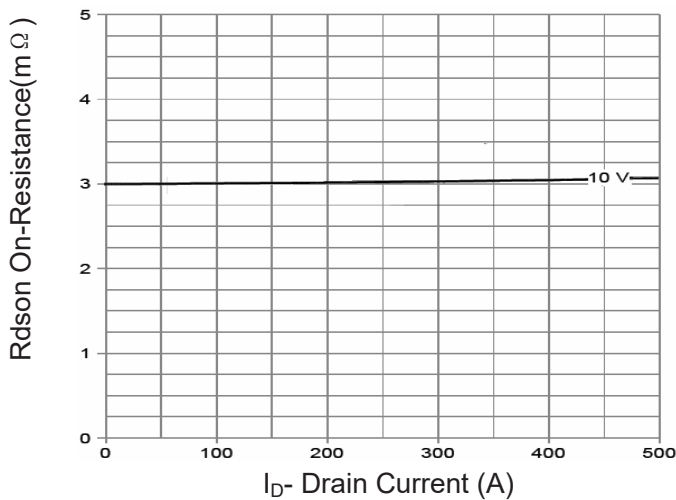
## Typical Electrical and Thermal Characteristics



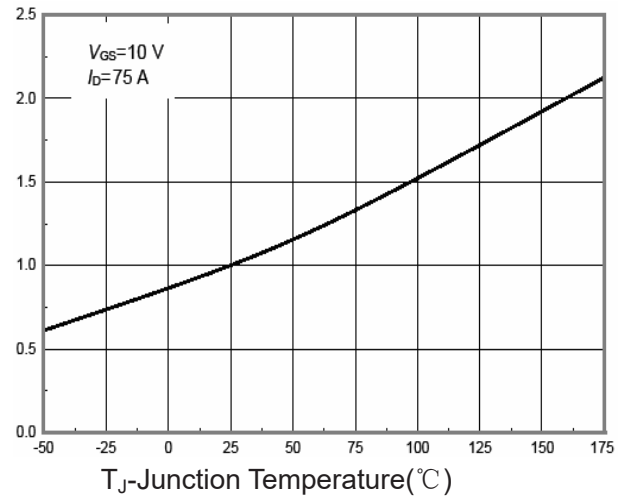
**Figure 1 Output Characteristics**



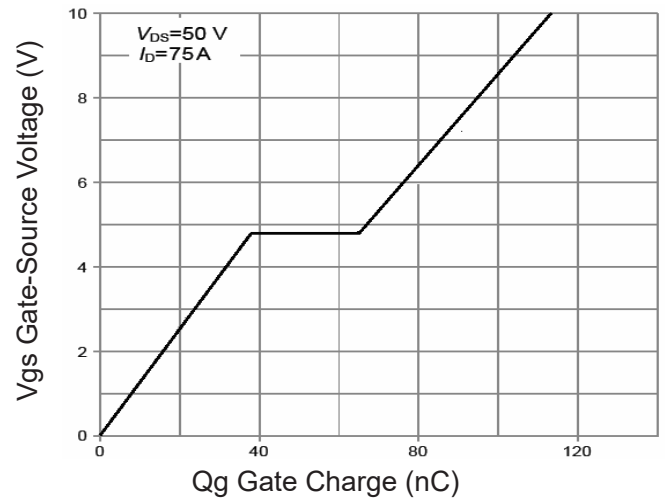
**Figure 2 Transfer Characteristics**



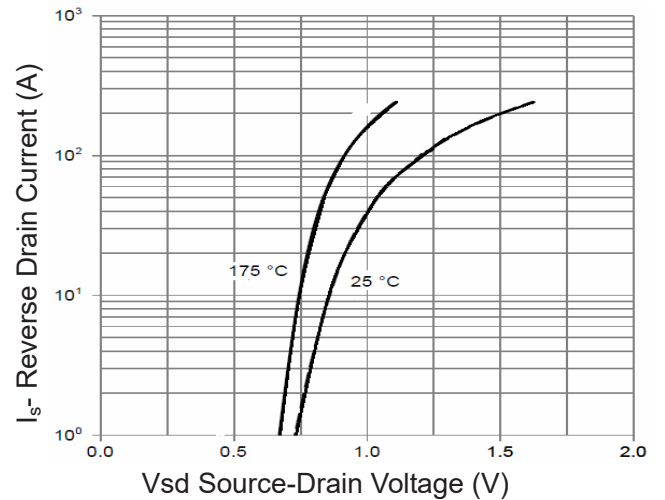
**Figure 3 Rdson- Drain Current**



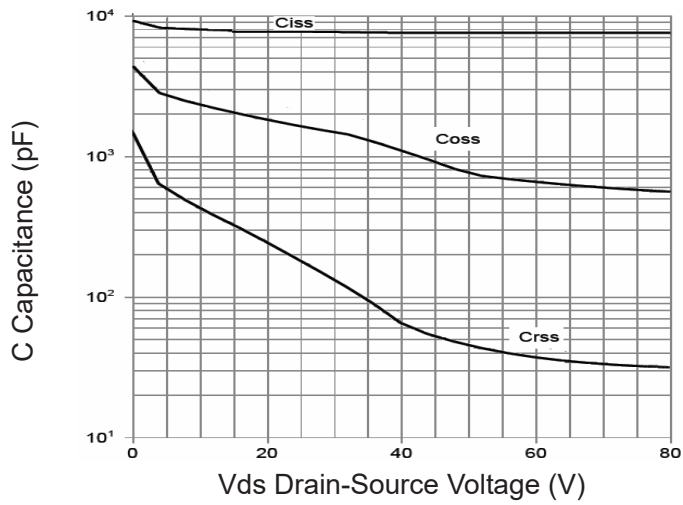
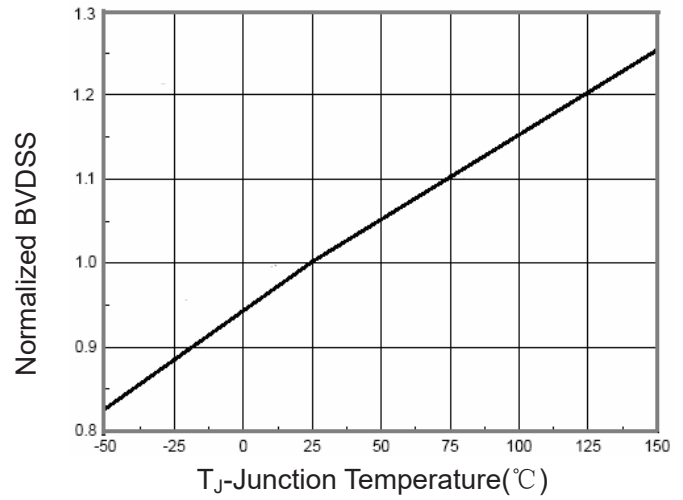
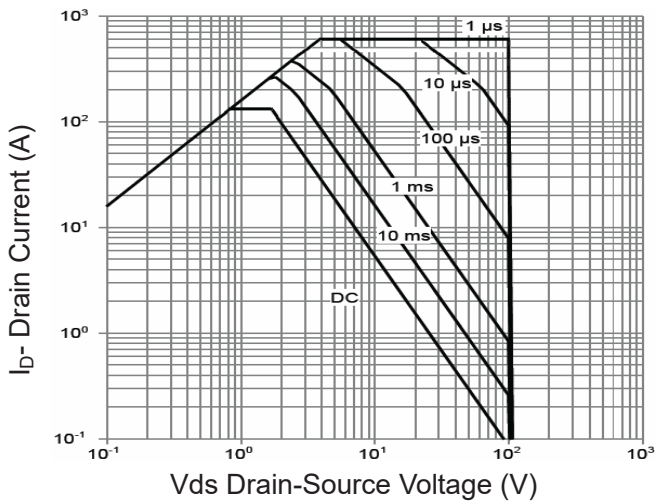
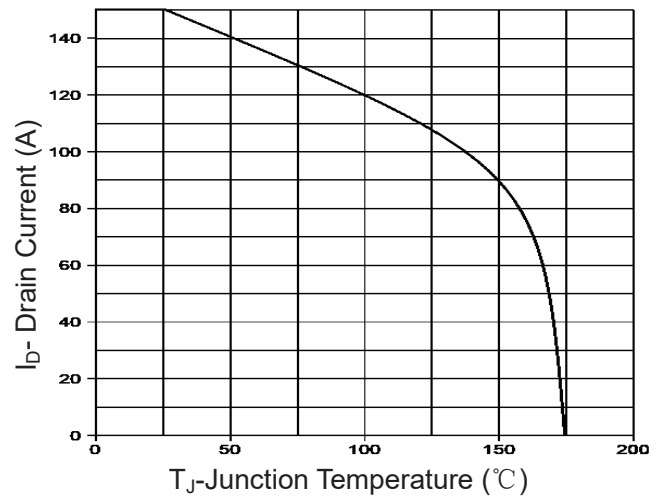
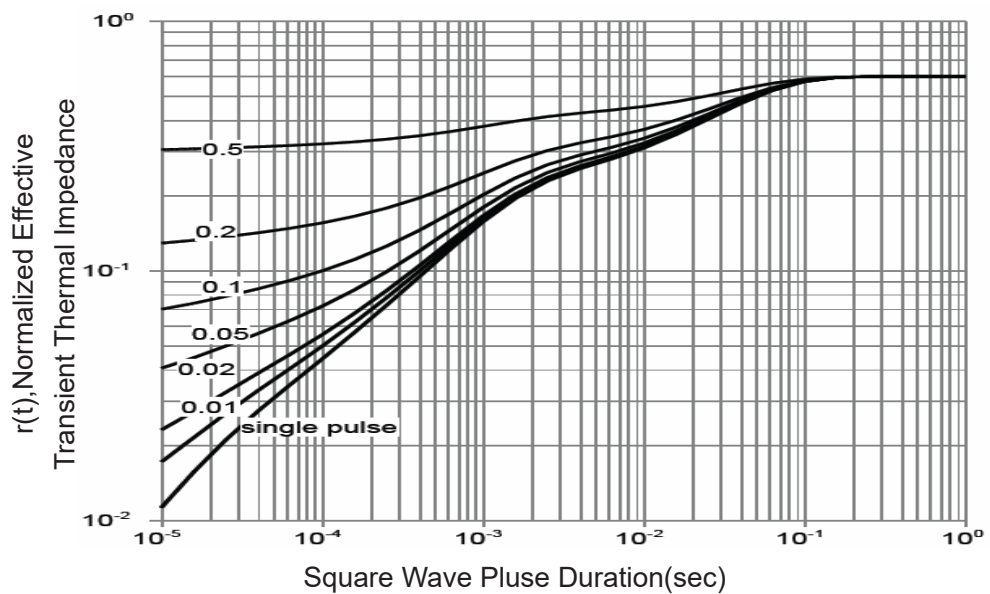
**Figure 4 Rdson-Junction Temperature**



**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**


**Figure 7 Capacitance vs Vds**

**Figure 9  $BV_{DSS}$  vs Junction Temperature**

**Figure 8 Safe Operation Area**

**Figure 10 Current De-rating**

**Figure 11 Normalized Maximum Transient Thermal Impedance**